citc

GBJ10005 THRU GBJ1010

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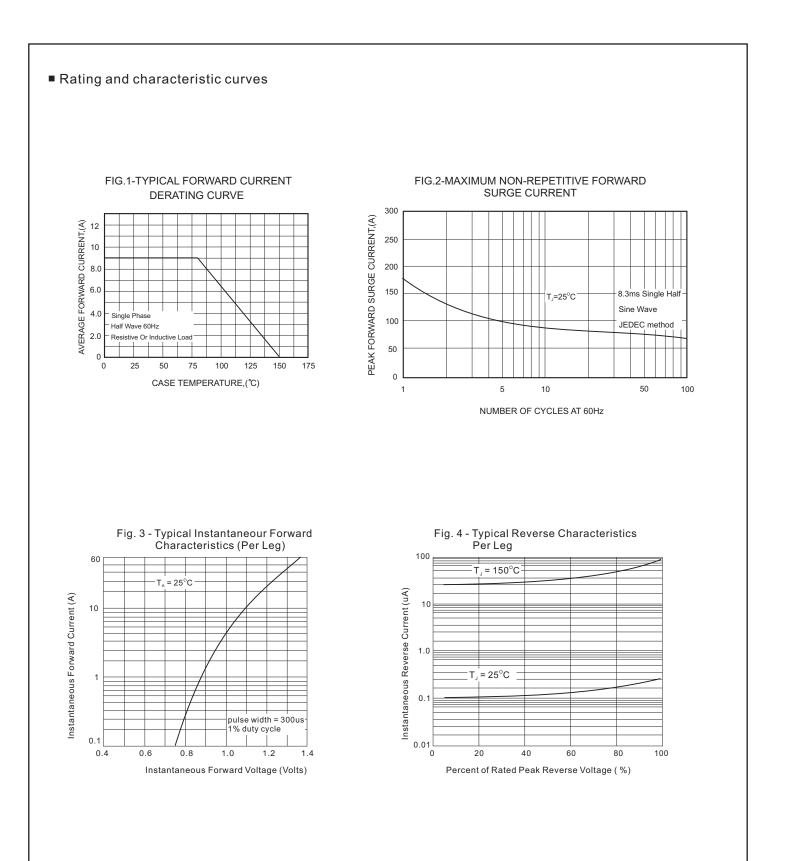
10A Miniature Glass Passivated Single-Phase Bridge Rectifiers

i outui	es			Outline	9					
Recomm Ideal for	erload ratings to ended for non-a & save space on le for automatic	utomatic appli printed circuit	cations.	GBJ						
 Reliable technolo Glass pa 	low cost constru gy results in ine ssivated chip jui	action utilizing expensive prodenctions.	uct.	hole for #6 screw	1.19	93(30.3) 59(29.7)	1. (1) (1) (1) (1) (1) (1) (1) (1) (1) (1)	73(4.4)	.150(3.8) .134(3.4) .134(3.4) .122(3.1)	
	" indicates Halo e parts meet Ro		ex.GBJ10005G. ts.	. <u>106(2.7)</u> .096(2.3) . <u>094(2.4)</u> .078(2.0)			65(4.2) 50(3.8) 		 ▲ ▲	
Mecha	anical data		$\begin{array}{c c} 0.043(1.1) \\ \hline 0.035(0.9) \\ \hline \end{array} \\ \hline $ \\ \hline \end{array} \\ \hline \\ \hline \end{array} \\ \\ \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \\ \\ \hline \end{array} \\ \\ \hline \end{array} \\ \\ \\ \hline \end{array} \\ \\ \hline \end{array} \\ \\ \\ \hline \end{array} \\ \\ \hline \\ \hline \\ \hline \\ \hline \\ \hline \\ \\ \hline \end{array} \\ \\ \\ \\ \hline \end{array} \\ \\ \\ \\ \\ \end{array} \\ \\ \\ \\						.023(0.6) 1.2)	
• Epoxy:U	L94-V0 rated fla	me retardant					70	.425(10	0.8)	
	olded plastic, Gl				<u>.402</u> .386	<u>.303</u> <u>.303</u> .287 <u>.287</u>	.69	08(18.0) 09(17.0)		
• Terminal	s : Solder plated MIL-STD-750	l, solderable pe 0, Method 2026			<u>(10.2)</u> (9.80)	$\frac{(7.7)}{(7.3)} \frac{(7.7)}{(7.3)}$				
• Polarity :	marked on body	,	5							
	Position : Any				Dimensio	ns in inche	es and (mi	llimeters)		
• Weight :	Approximated 7	'.00 gram								
■ Maxim	um ratinas a	nd electrica	I characteristic	9						
Rating at 2	-	mperature unl	I characteristic: ess otherwise spe %.	S cified. Single phase,	, half wav		resistive	or inductiv	ve load.	
Rating at 2 For capac Pa	25°C ambient te itive load, derate rameter	mperature unl	ess otherwise spe %.	cified. Single phase, Conditions	, half wav	e, 60Hz, i Symbol	esistive MIN.	or inductiv	ve load. MAX.	UNIT
Rating at 2 For capac Pa	25°C ambient te itive load, derate	mperature unl	ess otherwise spe %. with heatsink T _c =	cified. Single phase, Conditions 80°C				1	1	UNIT A
Rating at 2 For capac Pa	25°C ambient te itive load, derate rameter tified current	mperature unl	ess otherwise spe %. with heatsink T _c =	cified. Single phase, Conditions 80°C sine-wave superimpo		Symbol		1	MAX.	
Rating at 2 For capac Pa Forward rec Forward sur	25°C ambient te itive load, derate rameter tified current ge current	mperature unl	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single halfs rate load (JEDEC $V_R = V_{RRM} T_A = 25$	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C		Symbol I _o I _{FSM}		1	MAX. 10	A
Rating at 2 For capac Pa Forward rec Forward sur	25°C ambient te itive load, derate rameter tified current ge current	mperature unl	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single half s rate load (JEDEC $V_R = V_{RRM} T_A = 25$ $V_R = V_{RRM} T_A = 12$	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C 25°C		Symbol I _o I _{FSM}		1	MAX. 10 170	A
Rating at 2 For capac Pa Forward rec Forward sur Reverse cur	25°C ambient te itive load, derate rameter tified current ge current rent	mperature unl	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single halfs rate load (JEDEC $V_R = V_{RRM} T_A = 25$	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C 25°C		Symbol I _o I _{FSM} I _R I ² t		1	MAX. 10 170 10	A
Rating at 2 For capac Pa Forward rec Forward sur Reverse cur Current squa	25°C ambient te itive load, derate rameter tified current ge current rent ared time	mperature unl	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single half s rate load (JEDEC $V_R = V_{RRM} T_A = 25$ $V_R = V_{RRM} T_A = 12$	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C 25°C °C		Symbol I _o I _{FSM}		1	MAX. 10 170 10 500	A A uA A ² S °C/W
Rating at 2 For capac Pa Forward rec Forward sur Reverse cur Current squa Thermal res	25°C ambient te itive load, derate rameter tified current ge current rent ared time istance	mperature unl	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single halfs rate load (JEDEC $V_R = V_{RRM} T_A = 25$ $V_R = V_{RRM} T_A = 12$ t < 8.3ms, $T_J = 25$	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C 25°C °C		Symbol I _o I _{FSM} I _R I ² t		1	MAX. 10 170 10 500 120	A A uA A ² S
Rating at 2 For capac Pa Forward rec Forward sur Reverse cur Current squa Thermal res	25°C ambient te itive load, derate rameter tified current ge current rent ared time istance	mperature unl	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single half s rate load (JEDEC $V_R = V_{RRM} T_A = 25$ $V_R = V_{RRM} T_A = 12$ t < 8.3ms, $T_J = 25$ junction to ambien	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C 25°C °C	osed on	Symbol I _o I _{FSM} I _R I ² t R _{BJA}	MIN.	TYP.	MAX. 10 170 10 500 120 25	A A uA A ² S °C/W °C
Rating at 2 For capac Pa Forward rec Forward sur Reverse cur Current squa Thermal res Storage tem	25°C ambient te itive load, derate rameter tified current ge current rent ared time istance perature	Max. repetitive pear	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single half s rate load (JEDEC $V_R = V_{RRM} T_A = 25$ $V_R = V_{RRM} T_A = 12$ t < 8.3ms, $T_J = 25$ junction to ambien	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C 25°C 25°C °C t Max. DC blocking voltage	osed on	Symbol I_o I_{FSM} I_R $I^2 t$ R_{BJA} T_{STG} forward 2 $25A, T_A = 2$	MIN.	TYP.	MAX. 10 170 10 500 120 25 +150	A A uA A ² S °C/W °C
Rating at 2 For capac Pa Forward rec Forward sur Reverse cur Current squa Thermal res Storage tem Symbol	25°C ambient te itive load, derate rameter tified current ge current rent ared time istance perature	Max. repetitive pea reverse voltag V _{RRM} (V)	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single half s rate load (JEDEC $V_R = V_{RRM} T_A = 25$ $V_R = V_{RRM} T_A = 12$ t < 8.3ms, $T_J = 25$ junction to ambien	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C 25°C °C t Max. DC blocking voltage V _R (V)	osed on	Symbol I_o I_{FSM} I_R $I^2 t$ R_{BJA} T_{STG} forward 2 $25A, T_A = 2$	MIN.	TYP.	MAX. 10 170 10 500 120 25 +150	A A uA A ² S °C/W °C
Rating at 2 For capac Pa Forward rec Forward sur Reverse cur Current squa Thermal res Storage tem Symbol GBJ10005	25°C ambient te titive load, derate rameter tified current ge current rent ared time istance perature Marking code GBJ10005	Max. repetitive pear reverse voltag V _{RRM} (V) 50	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single half s rate load (JEDEC) $V_R = V_{RRM} T_A = 25$ $V_R = V_{RRM} T_A = 12$ t < 8.3ms, $T_J = 25$ junction to ambien	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C 25°C °C t t Max. DC blocking voltage V _R (V) 50	osed on	Symbol I_o I_{FSM} I_R $I^2 t$ R_{BJA} T_{STG} forward 2 $25A, T_A = 2$	MIN.	TYP.	MAX. 10 170 10 500 120 25 +150	A A uA A ² S °C/W °C
Rating at 2 For capac Pa Forward rec Forward sur Reverse cur Current squa Thermal res Storage tem Symbol GBJ10005 GBJ1001	25°C ambient te itive load, derate rameter tified current ge current rent ared time istance perature Marking code GBJ10005 GBJ1001	Max. repetitive pear reverse voltag V _{RRM} (V) 50 100	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single half s rate load (JEDEC) $V_R = V_{RRM} T_A = 25$ $V_R = V_{RRM} T_A = 12$ t < 8.3ms, $T_J = 25$ junction to ambien Max. RMS voltage $V_{RMS}(V)$ 35 70	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C 25°C °C t Max. DC blocking voltage V _R (V) 50 100	osed on	Symbol I_o I_{FSM} I_R $I^2 t$ R_{BJA} T_{STG} forward 2 $25A, T_A = 2$	MIN.	TYP.	MAX. 10 170 10 500 120 25 +150	A A uA A ² S °C/W °C
Rating at 2 For capac Pa Forward rec Forward sur Reverse cur Current squa Thermal res Storage tem Symbol GBJ10005 GBJ1001 GBJ1002	25°C ambient te titive load, derate rameter tified current ge current rent ared time istance perature Marking code GBJ10005 GBJ1001 GBJ1002	Max. repetitive pea reverse volta V _{RRM} (V) 50 100 200	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single half s rate load (JEDEC $V_R = V_{RRM} T_A = 25$ $V_R = V_{RRM} T_A = 12$ t < 8.3ms, $T_J = 25$ junction to ambien ak ge Max. RMS voltage $V_{RMS} (V)$ 35 70 140	cified. Single phase, Conditions 80°C sine-wave superimpore method) 5°C 25°C °C t Max. DC blocking voltage V _R (V) 50 100 200	osed on	Symbol I_o I_{FSM} I_R $I^2 t$ $R_{\theta JA}$ T_{STG} . forward $25A, T_A = 2$ $V_F (V)$	MIN.	TYP.	MAX. 10 170 10 500 120 25 +150 rating tem T _J (°C)	A A uA A ² S °C/W °C
Rating at 2 For capac Pa Forward rec Forward sur Reverse cur Current squa Thermal res Storage tem Symbol GBJ10005 GBJ1001 GBJ1002 GBJ1004	25°C ambient te itive load, derate rameter tified current ge current rent ared time istance perature Marking code GBJ10005 GBJ1001 GBJ1002 GBJ1004	Max. repetitive pea reverse voltag V _{RRM} (V) 50 100 200 400	ess otherwise spe %. with heatsink $T_c =$ 8.3ms single halfs rate load (JEDEC) $V_R = V_{RRM} T_A = 25$ $V_R = V_{RRM} T_A = 12$ $t < 8.3ms, T_J = 25$ junction to ambien Max. RMS voltage $V_{RMS}(V)$ 35 70 140 280	cified. Single phase, Conditions 80°C sine-wave superimpo method) 5°C 25°C °C t Max. DC blocking voltage V _R (V) 50 100 200 400	osed on	Symbol I_o I_{FSM} I_R $I^2 t$ $R_{\theta JA}$ T_{STG} . forward $25A, T_A = 2$ $V_F (V)$	MIN.	TYP.	MAX. 10 170 10 500 120 25 +150 rating tem T _J (°C)	A A uA A ² S °C/W °C



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